

Supplementary information

Amorphous zinc-doped silicon oxide (SZO) resistive switching memory: manipulated bias control from selector to memristor

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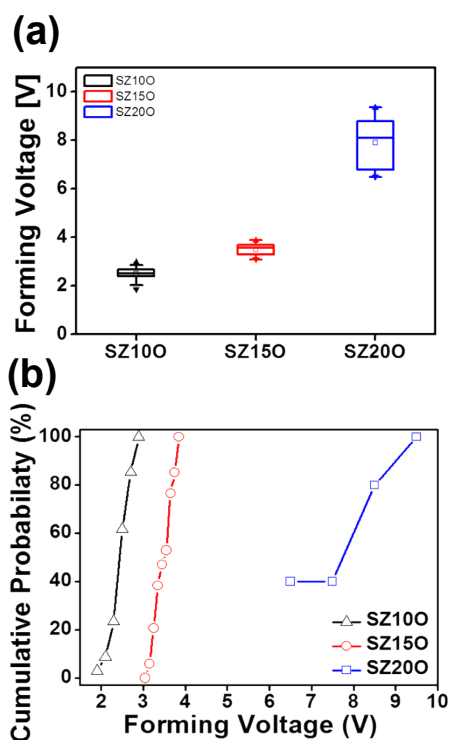


Figure S1 (a) Box chart of forming voltages at different fabrication conditions. (b) Cumulative probability of forming voltages obtained from different fabrication conditions.

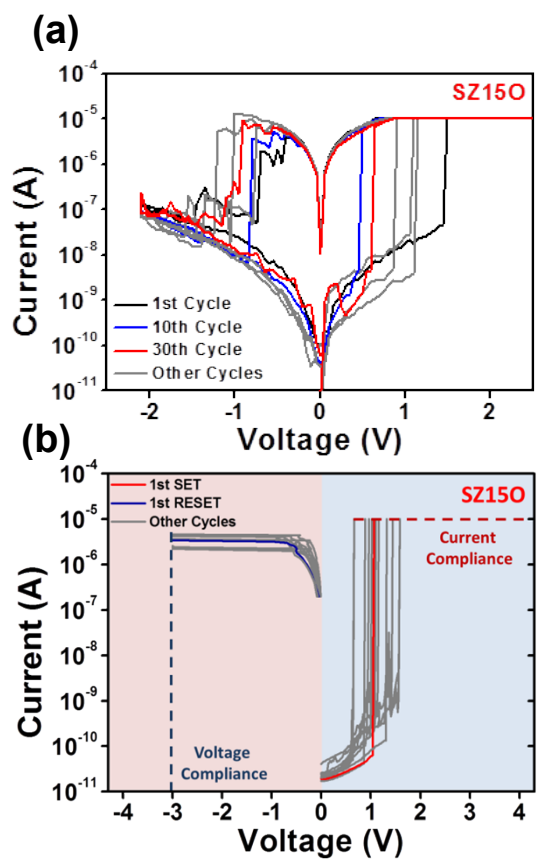


Figure S2 (a) A ‘butterfly’ shape operation mode for 30 cycles. **(b)** 100-cycle endurance results from V-SET and i-RESET operation modes.